### **ABSOLUTE MAXIMUM RATINGS**

(Voltages referenced to GND. Note 1.)	
V <sub>DD</sub> , A_, B_, SW_, EFN	0.3V to +6.0V
All Other Pins (except GND)	0.3V to $V_{DD}$ + 0.3V
Continuous Current, A_, B	±60mA
Continuous Current, V <sub>DD</sub> or GND	±100mA

Note 1: EFN must be either connected to VDD or left unconnected. EFN must not be connected to ground.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = +5V \pm 10\%, T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ ,  $V_{DD} = +5V$ . Note 2.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNIT	
Power-Supply Voltage	V <sub>DD</sub>		4.5	5	5.5	V	
Power-Supply Current	IDD	EFN = unconnected; all inputs = 0; all outputs high or low, no loads			10	μA	
EFN Leakage Current	١L	$V_{EFN} = V_{DD} - 0.2V$	-2		+2	μA	
LOGIC INPUTS (DA_, DB_, MODE, A	\D_)						
Input Low Voltage DA_, DB_	VIL	MODE = 0V			0.8	V	
Input High Voltage DA_, DB_	VIH	MODE = 0V	2			V	
Input-Voltage Hysteresis DA_, DB_	V <sub>HYST</sub>	MODE = 0V		150		mV	
Input Low Voltage AD_	VIL	$MODE = V_{DD}$			0.8	V	
Input High Voltage AD_	VIH	$MODE = V_{DD}$	2			V	
Input-Voltage Hysteresis AD_	V <sub>HYST</sub>	$MODE = V_{DD}$		150		mV	
Input Low Voltage MODE	VIL				0.8	V	
Input High Voltage MODE	VIH		2			V	
Input-Voltage Hysteresis MODE	V <sub>HYST</sub>			150		mV	
Input Leakage Current DA_, DB_	١L	MODE = 0V			±1	μA	
Input Leakage Current AD_	١L	$MODE = V_{DD}$			±1	μΑ	
Input Leakage Current MODE	١L				±1	μA	
LOGIC OUTPUTS DO_							
Output-Voltage Low	VOL	MODE = $V_{DD}$ , $I_{SINK}$ = 30 $\mu$ A			0.5	V	
Output-Voltage High	VOH	MODE = $V_{DD}$ , $I_{SOURCE} = 26\mu A$	2			V	
Output Leakage Current	١٢	$\begin{array}{l} \text{MODE} = \text{V}_{\text{DD}} \text{, output at high impedance,} \\ \text{V}_{\text{IN}} = 1.5 \text{V} \end{array}$			±1	μA	
Output Rise Time	t <sub>R</sub>	$V_{OUT}$ from 0.8V to 2.2V, $C_{LOAD} = 10$ pF		600		ns	
Output Short Circuit Ourrant		ISOURCE			-1		
Output Short-Circuit Current	ISC	ISINK			+3	mA	

## **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +5V \pm 10\%, T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ ,  $V_{DD} = +5V$ . Note 2.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNIT
ANALOG SWITCHES	•		•			
On-Resistance Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	R <sub>ON</sub>	$V_{IN} = 2.5V, I_{IN} = \pm 10mA$		12		Ω
On-Resistance-Flatness Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	R <sub>FLAT</sub>	V <sub>IN</sub> = 0.8V, 2.5V, 3.7V		2.5		Ω
On-Channel -3dB Bandwidth Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	BW	$R_S = R_L = 50\Omega$ , $C_L = 35pF$ , Figure 1		190		MHz
Off-Isolation Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	V <sub>ISO</sub>	$R_S = R_L = 50\Omega$ , f = 1MHz, Figure 1		65		dB
Crosstalk Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	V <sub>CT</sub>	$R_S = R_L = 50\Omega$ , f = 1MHz, Figure 1		75		dB
On-Capacitance Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	C <sub>ON</sub>	V <sub>DD</sub> = 4.5V, f = 1MHz, Figure 2		37		pF
Off-Capacitance Standard Switches: A[1], A[2], A[3], B[1], B[2], B[3]	COFF	V <sub>DD</sub> = 4.5V, f = 1MHz, Figure 2		15		pF
Charge Injection	Q	$V_{GEN}$ = 1.5V, $R_{GEN}$ = 0 $\Omega$ , $C_L$ = 100pF, Figure 3		13		рС
On-Resistance +5V/Drain: A[0], A[4], B[0], B[4]	R <sub>ON</sub>	$V_{DD}$ = 4.5V, $V_{IN}$ = 0V or $V_{DD}$		3		Ω
Switch Leakage Current	١L				±10	μA
I <sup>2</sup> C SPECIFICATIONS (SDA, SCL, MC	DDE = V <sub>DD</sub> )					
Input Low Voltage	VIL				0.8	V
Input High Voltage	VIH		2.4			V
Input-Voltage Hysteresis	VHYST			450		mV
Input Leakage Current	١L				±1	μA
Output-Voltage Low SDA	V <sub>OL</sub>	I <sub>SINK</sub> = 3mA			0.4	V
TIMING CHARACTERISTICS (Figure	4), MODE =	V <sub>DD</sub>				
Serial Clock Frequency	fSCL	$V_{DD} = 4.5V$	100	400		kHz
Hold Time (Repeated) START Condition (after this period the first clock pulse is generated)	<sup>t</sup> HD,STA	f <sub>SCL</sub> = 100kHz	4			μs
Low Period of the SCL Clock	tLOW	f <sub>SCL</sub> = 100kHz	4.7			μs
	1	I	1			1

## ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +5V \pm 10\%, T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ ,  $V_{DD} = +5V$ . Note 2.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	МАХ	UNIT
High Period of the SCL Clock	thigh	$f_{SCL} = 100 kHz$	4			μs
Setup Time for a Repeated START Condition	<sup>t</sup> SU,STA	f <sub>SCL</sub> = 100kHz	4.7			μs
Data Hold Time	thd,dat	f <sub>SCL</sub> = 100kHz	25			μs
Data Setup Time	tsu,dat	$f_{SCL} = 100 kHz$	250			ns
ESD PROTECTION (HUMAN BODY M	ESD PROTECTION (HUMAN BODY MODEL)					
SW_, A_, B_	ESD	Referenced to GND		±6		kV
All Other I/Os	ESD			±2		ĸv

**Note 2:** Limits at  $T_A = -40^{\circ}C$  are guaranteed by design.



Figure 1. On-Loss, Off-Isolation, and Crosstalk



Figure 2. Channel Off-/On-Capacitance



Figure 3. Charge Injection



5

**MAX4814E** 



-20

-40

-60

-80

-100

0.1

ON-LOSS

CROSS-TAI k

10

FREQUENCY (MHz)

1

100

1000

**MAX4814E** 

6

0.3 0.25

0.2

0.15

0.1

0.05

0

-40

 $V_{DD} = 4.5V$ 

35

TEMPERATURE (°C)

10

SWITCH I/O\_ = 0V

-15

 $V_{DD} = 5.0V$ 

60

85

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## Pin Description

PIN	NAME	FUNCTION
1, 16, 24, 25, 33, 48, 56, 57	GND	Ground. Must connect all GND pins together.
2, 15, 34	I.C.	Internally Connected. Leave I.C. unconnected
3	A[0]	Switch A I/O 0. A[0] has a 3 $\Omega$ (typ) resistance to switch 5V or drain.
4	A[1]	Switch A I/O 1. A[1] has a $12\Omega$ (typ) resistance to switch data.
5	A[2]	Switch A I/O 2. A[2] has a $12\Omega$ (typ) resistance to switch data.
6	A[3]	Switch A I/O 3. A[3] has a $12\Omega$ (typ) resistance to switch data.
7	A[4]	Switch A I/O 4. A[4] has a $3\Omega$ (typ) resistance to switch 5V or drain.
8, 9, 17, 32, 40, 41, 49, 64	V <sub>DD</sub>	Positive-Supply Voltage Input. Connect $V_{DD}$ to a +5V supply voltage. Bypass $V_{DD}$ to GND with a 0.1µF capacitor. Must connect all $V_{DD}$ pins together.
10	B[0]	Switch B I/O 0. B[0] has a $3\Omega$ (typ) resistance to switch 5V or drain.
11	B[1]	Switch B I/O 1. B[1] has a $12\Omega$ (typ) resistance to switch data.
12	B[2]	Switch B I/O 2. B[2] has a 12 $\Omega$ (typ) resistance to switch data.
13	B[3]	Switch B I/O 3. B[3] has a $12\Omega$ (typ) resistance to switch data.
14	B[4]	Switch B I/O 4. B[4] has a $3\Omega$ (typ) resistance to switch 5V or drain.
18	MODE	MODE Selection Input. Connect MODE to $V_{DD}$ (MODE = 1) to select I <sup>2</sup> C control mode. Connect MODE to GND (MODE = 0) to select direct-control mode.
19	SDA	I <sup>2</sup> C-Compatible Serial Data I/O
20	SCL	I <sup>2</sup> C-Compatible Serial Clock Input
21	AD0	Programmable I <sup>2</sup> C Address Bit. AD[0] sets the I <sup>2</sup> C address of the device. User- selectable device address bit, LSB, LSB+1, MSB (see Figure 5).
22	AD1	Programmable I <sup>2</sup> C Address Bit. AD[1] sets the I <sup>2</sup> C address of the device. User- selectable device address bit, LSB, LSB+1, MSB (see Figure 5).
23	AD2	Programmable I <sup>2</sup> C Address Bit. AD[2] sets the I <sup>2</sup> C address of the device. User- selectable device address bit, LSB, LSB+1, MSB (see Figure 5).
26	SW3[4]	Switch 3 I/O 4
27	SW3[3]	Switch 3 I/O 3
28	SW3[2]	Switch 3 I/O 2
29	SW3[1]	Switch 3 I/O 1
30	SW3[0]	Switch 3 I/O 0
31, 50	EFN	ESD Protection. Connect EFN with an external $0.1\mu$ F capacitor to GND for ±15kV ESD HBM protection. The capacitor from EFN to GND provides an additional discharge path for the ESD energy.
35	SW2[4]	Switch 2 I/O 4
36	SW2[3]	Switch 2 I/O 3
37	SW2[2]	Switch 2 I/O 2
38	SW2[1]	Switch 2 I/O 1
39	SW2[0]	Switch 2 I/O 0
42	SW1[4]	Switch 1 I/O 4
43	SW1[3]	Switch 1 I/O 3
44	SW1[2]	Switch 1 I/O 2



## Pin Description (continued)

PIN	NAME	FUNCTION
45	SW1[1]	Switch 1 I/O 1
46	SW1[0]	Switch 1 I/O 0
47	N.C.	No Connection. Not internally connected.
51	SW0[4]	Switch 0 I/O 4
52	SW0[3]	Switch 0 I/O 3
53	SW0[2]	Switch 0 I/O 2
54	SW0[1]	Switch 0 I/O 1
55	SW0[0]	Switch 0 I/O 0
58	DA0/DO0	Direct-Control Bit I/O. In mode 0, DA0/DO0 is set as an input, DA0, to control switch connections. In mode 1, DA0/DO0 is set as an output, DO0. The output bits are used to drive the MAX3845.
59	DA1/DO1	Direct-Control Bit I/O. In mode 0, DA1/DO1 is set as an input, DA1, to control switch connections. In mode 1, DA1/DO1 is set as an output, DO1. The output bits are used to drive the MAX3845.
60	DA2/DO2	Direct-Control Bit I/O. In mode 0 DA2/DO2 is set as an input, DA2, to control switch connections. In mode 1, DA2/DO2 is set as an output, DO2. The output bits are used to drive the MAX3845.
61	DB0/DO3	Direct-Control Bit I/O. In mode 0 DB0/DO3 is set as an input, DB0, to control switch connections. In mode 1, DB0/DO3 is set as an output, DO3. The output bits are used to drive the MAX3845.
62	DB1	Direct-Control Bit I/O. In mode 0, DB1 is set as an input. In mode 1, DB1 is high impedance.
63	DB2	Direct-Control Bit I/O. In mode 0, DB2 is set as an input. In mode 1, DB2 is high impedance.
EP	EP	Exposed Pad. Connect exposed pad to ground. For enhanced thermal dissipation, connect EP to a copper area as large as possible. Do not use EP as a sole ground connection.

## **Detailed Description**

The MAX4814E provides routing for low-frequency DVI/HDMI signals. The MAX4814E is a bidirectional 2:4 DVI/HDMI switch. Each switch consists of five single-pole/single-throw (SPST) channels. The channels have a low  $3\Omega$  (typ) on-resistance to route +5V and drain, and three channels to route data. Channels A0, A4, B0, B4, SW\_0, and SW\_4 have a  $3\Omega$  (typ) on-resistance to route +5V and drain, and the remaining channels A1–A3, B1–B3, SL0\_3, and SW\_1 have a  $12\Omega$  (typ) on-resistance to route data. The device features a mode input to control the device using direct-control logic inputs or an I<sup>2</sup>C interface. Connect MODE to GND to control the device using I<sup>2</sup>C. In I<sup>2</sup>C mode, the MAX4814E controls the MAX3845 (see Figure 5).

### **Analog Signal Levels**

Signal inputs over the full voltage range (OV to  $V_{DD}$ ) are passed through the switch with minimal change in onresistance (see the *Typical Operating Characteristics*). The switches are bidirectional. Therefore, switch A\_, switch B\_, and switch SW\_ can be either inputs or outputs.

### Switch Control

The MAX4814E features a mode input to control the device through either an I<sup>2</sup>C interface or through directcontrol logic inputs. Connect MODE to GND (mode 0) to control the device using the direct-control inputs DA\_ and DB\_ (see Table 1 and Figure 6). Connect MODE to V<sub>DD</sub> (mode 1) to control the device using the I<sup>2</sup>C interface.

#### Direct Control Method (Mode 0)

In mode 0, DA0/DO0 becomes input DA0, DA1/DO1



## \_Functional Diagram

**MAX4814E** 

becomes input DA1, DA2/DO2 becomes input DA2, and DB0/DO3 becomes input DB0. Inputs DB1 and DB2 are enabled.

In mode 0, the direct-control inputs DA\_ and DB\_ are used to control the connection of the switches. DA2 is

used as the enable for switch A, and DB2 is used as the enable for switch B. Connecting DA2 to V<sub>DD</sub> enables switch A, and connecting DA2 to GND disables switch A. Connecting DB2 to V<sub>DD</sub> enables switch B, and connecting DB2 to GND disables switch B. Inputs DA0 and

DA1 select the connections of switch A to switch SW\_ and inputs DB0 and DB1. Select the connections of switch B to SW\_. See Table 3a for the pin configuration and Table 3b for a complete summary.

#### I<sup>2</sup>C Interface Method (Mode 1)

In mode 1, the switch connections are controlled through the I<sup>2</sup>C interface. Inputs SDA and SCL program registers R0 and R1. Register R0, bits [7 to 2], select the connection of switch A and switch B to switch SW\_ (see the  $I^2C$  Registers and Bit Descriptions section).

The bits of register R1 transfer data to the output DO\_. The data on output DO\_ is used to communicate with the MAX3845. In mode 1, DA0/DO0 becomes output DO0, DA1/DO1 becomes output DO1, DA2/DO2 becomes output DO2, and DB0/DO3 becomes output DO3. DB1 and DB2 are high impedance. See Table 3a for the pin configuration. See Table 4 for register R1 to DO\_ output mapping.

### \_I<sup>2</sup>C Registers and Bit Descriptions

Two internal registers (RO and R1) program the MAX4814E. Table 2 lists both registers, their addresses, and power-up default states. Both registers are read/write registers.

In register R0, bit BAEN is used as the enable for switch A, and bit BBEN is used as the enable for switch B. Writing 1 to bit BAEN enables switch A; and writing 0 to bit BAEN disables switch A. Writing 1 to bit BBEN enables switch B, and writing 0 to bit BBEN disables switch B. BASEL1 and BASEL0 select the connections of switch A to switch SW\_, while BBSEL1 and BBSEL0 select the connections of switch B to switch SW\_, as summarized in Table 6.

#### I<sup>2</sup>C Register R0 Two LSB Bits

The two LSBs are hard coded as 00. Register R0 ignores any value written to the two LSBs; anytime register R0 is read the hard-coded values are returned.

#### Bank A Enable (BAEN) and Bank B Enable (BBEN) Bits 1 = Enable

#### 0 = Disable

#### Bank A Select (BASEL1/BASEL0) and Bank B Select (BBSEL1/BBSEL0) Bits

Bits BASEL1 and BASEL0 select the switch SW\_ that switch A is connected to. Bits BBSEL1 and BBSEL0 select the switch SW\_ that switch B is connected to (see Table 6).

#### **Power-On Default States**

When power is applied to the MAX4814E internal power-on reset (POR), circuitry sets registers R0 and R1 to their default states. Register R0 is set to all zeros, or 00h, and register R1 is set to 10101010, or AAh, as shown in Table 2.

Having all zeros in register R0 disables both banks A and B; see Table 6 for register R0 to switch mapping. Setting register R1 to AAh forces the outputs at DO\_ to be high impedance.

**Note:** The output, DO\_ is used to communicate with the MAX3845 when the MAX4814E is being used without its companion. The MAX3845 and the MAX4814E use the I<sup>2</sup>C interface (MODE = 1). All DO\_ outputs need to be connected through a 10k $\Omega$  resistor to GND.

INPUT PIN	OPERATION	
MODE	OPERATION	
0	Puts the device in mode 0. The direct-control inputs DA_ and DB_ control the switches.	
1	Puts the device in mode 1. The switches are controlled by the I <sup>2</sup> C interface. DO_ becomes an active output. Inputs DB1 and DB2 are high impedance.	

DECICTED		BIT								POWE	R-UP
REGISTER	7	6	5	4	3	2	1	0	ADDRESS	BINARY	HEX
R0	BBEN	BBSE L1	BBSEL0	BAEN	BASEL1	BASE L0	х	Х	0x00	0000 0000	00
R1	DO3 High Impedance	DO3 Data	DO2 High Impedance	DO2 Data	DO1 High Impedance	DO1 Data	DO0 High Impedance	DO0 Data	0x01	1010 1010	AA

### Table 1. Mode Configuration

Table 2, I<sup>2</sup>C Register Map

*X* = Hardwired code, not programmable by user.



### Table 3a. Input/Output Configurations for DA\_, DB\_, and DO\_

MODE	PIN CONFIGURATION						
MODE	DA0/DO0	DA1/DO1	DA2/DO2	DB0/DO3	DB1	DB2	
0	DA0, Input	DA1, Input	DA2, Input	DB0, Input	DB1, Input	DB2, Input	
1	DO0, Output	DO1, Output	DO2, Output	DO3, Output	High Impedance	High Impedance	

### Table 3b. Mode 0 Direct-Control Configurations

PIN CONNECTION	OPERATION					
DA2	OFENATION					
0	Bank A switches are disabled					
1	Bank A switches are enabled. Switch A connections depend on the DA0 and DA1 inputs.					

PIN CONNECTION	ODEDATION					
DB2	OPERATION					
0	Bank B switches are disabled					
1	Bank B switches are enabled. Switch B connections depend on the DB0 and DB1 inputs.					

	PIN CONNECTION		005		
DB1	DB0	DA1	DA0		RATION
0	0	0	0	Connect A to SW0	B is high impedance
0	0	0	1	Connect A to SW1	Connect B to SW0
0	0	1	0	Connect A to SW2	Connect B to SW0
0	0	1	1	Connect A to SW3	Connect B to SW0
0	1	0	0	Connect A to SW0	Connect B to SW1
0	1	0	1	Connect A to SW1	B is high impedance
0	1	1	0	Connect A to SW2	Connect B to SW1
0	1	1	1	Connect A to SW3	Connect B to SW1
1	0	0	0	Connect A to SW0	Connect B to SW2
1	0	0	1	Connect A to SW1	Connect B to SW2
1	0	1	0	Connect A to SW2	B is high impedance
1	0	1	1	Connect A to SW3	Connect B to SW2
1	1	0	0	Connect A to SW0	Connect B to SW3
1	1	0	1	Connect A to SW1	Connect B to SW3
1	1	1	0	Connect A to SW2	Connect B to SW3
1	1	1	1	Connect A to SW3	B is high impedance

Note: When switch A and switch B are connected to the same SW\_, switch A takes precedence and switch B is high impedance.

### I<sup>2</sup>C Interface

The MAX4814E features an I<sup>2</sup>C interface using a repeated start. The MAX4814E I<sup>2</sup>C interface refers to the I<sup>2</sup>C bus specification (version 2.1, Jan 2000).

**Device Address** able device addresses

The MAX4814E has selectable device addresses through external inputs. The slave address consists of four fixed bits (B7–B4, set to 0111) followed by three pin-programmable bits (AD2–AD0), as shown on Table 7.

PIN	REGISTER R1 (0x01)									OUTPUT PIN		
MODE	BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0	CONFIGURATION			
1	_	_	_	_		_	0	0	DO0	0		
1		_	_	_	_		0	1	DO0	1		
1	_	_	_	_	_	_	1	Х	DO0	Hi-Z		
1	—	—	—	—	0	0	—	—	DO1	0		
1	_	_	—	_	0	1	—	—	DO1	1		
1		_	_	_	1	Х	_	—	DO1	Hi-Z		
1	_	_	0	0		_	_	—	DO2	0		
1	_	_	0	1		_	_	—	DO2	1		
1	—	_	1	Х		—	_	—	DO2	Hi-Z		
1	0	0	_	—	—		_	—	DO3	0		
1	0	1	_	_	_	_	_	_	DO3	1		
1	1	Х	_		_				DO3	Hi-Z		

### Table 4. I<sup>2</sup>C Register R1 (0X01) to DO\_ Mapping

X = Don't care.

## Table 5. I<sup>2</sup>C Register R0 (0x00)

REGISTER R0 (0x00)									
BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0		
BBEN	BBSEL1	BBSEL0	BAEN	BASEL1	BASELO	Х	Х		

X = Hardwired, not programmed by user.

For example: If AD0, AD1, and AD2 are hardwired to ground, then the complete address is 0111000. The full address is defined as the seven most significant bits followed by the read/write bit. Set the read/write bit to 1 to configure the MAX4814E to read mode. Set the read/write bit to 0 to configure the MAX4814E to write mode. The address is the first byte of information sent to the MAX4814E after the START condition.

## **Applications Information**

#### **ESD** Protection

As with all Maxim devices, ESD-protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. Switch A, switch B, and switch SW\_ are further protected against static electricity. Maxim's engineers have developed state-of-the-art structures to protect these pins against ESD up to  $\pm 6$ kV without damage. The ESD structures withstand high ESD in normal operation, and when the device is powered down. ESD protection can be tested in various ways. The ESD protection of switch A, switch B, and switch SW\_ are characterized for  $\pm$ 6kV (Human Body Model) using the MIL-STD-883.

#### **ESD** Test Conditions

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

#### Human Body Model

Figure 7 shows the Human Body Model, and Figure 8 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest that is then discharged into the test device through a  $1.5k\Omega$  resistor.



MAX4814E

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	DA_, DB_ INPUTS/REGISTER R0 BITS							SWITCH A AND B TO SW_ CONNECTIONS						
DB2/ BBEN	DB1/ BBSEL1	DB0/ BBSEL0	DA2/ BAEN	DA1/ BASEL1	DA0/ BASEL0		B TO SW3	B TO SW2	B TO SW1	B TO SW0	A TO SW3	A TO SW2	A TO SW1	A TO SW0
0	Х	Х	0	Х	Х		—	_	_	_			_	
0	Х	Х	1	0	0									1
0	Х	Х	1	0	1								1	_
0	Х	Х	1	1	0		—					1		
0	Х	Х	1	1	1		—				1			
1	0	0	0	Х	Х		—	_		1	_	_		_
1	0	0	1	0	0		—	_	—	0	—	—	—	1
1	0	0	1	0	1		—			1			1	
1	0	0	1	1	0		—			1		1		
1	0	0	1	1	1		—			1	1			
1	0	1	0	Х	Х		—		1		—	—	—	_
1	0	1	1	0	0		—		1					1
1	0	1	1	0	1		—		0				1	
1	0	1	1	1	0		—		1			1		
1	0	1	1	1	1		—		1		1			
1	1	0	0	Х	Х			1						
1	1	0	1	0	0		—	1						1
1	1	0	1	0	1		—	1					1	
1	1	0	1	1	0		—	0				1		
1	1	0	1	1	1		_	1	_	_	1		_	
1	1	1	0	Х	Х		1	_			_	_	_	_
1	1	1	1	0	0		1	_			_	_	_	1
1	1	1	1	0	1		1	_	—	—	_	_	1	_
1	1	1	1	1	0		1	—	—	—		1	_	—
1	1	1	1	1	1		0				1			_

### **Table 6. Switch Selection Truth Table**

— = Denotes no connection.

1 = Denotes switch connection.

0 = Denotes switch B is high impedance.

X = Don't care.

### Table 7. MAX4814E Device Address

B7	B6	B5	B4	B3	B2	B1	B0
0	1	1	1	AD2	AD1	AD0	R/W
	Fix	ed			User Selected		—

### **Power-Supply Biasing and Sequencing**

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings, since stresses beyond the listed ratings can cause permanent damage to the device. Always sequence  $V_{DD}$  on first, followed by the switch inputs and the logic inputs. Bypass at least one  $V_{DD}$  input to ground with a  $0.1\mu F$  capacitor as close as possible to the device. Use the smallest physical size possible for optimal performance.

**MAX4814E** 



Figure 4. 2-Wire Interface Timing Diagram







Figure 7. Human Body ESD Test Model



Figure 6. Mode 0: Direct Control



Figure 8. Human Body Current Waveform





It is also recommended to bypass more than one  $V_{DD}$  input. A good strategy is to bypass one  $V_{DD}$  input with a 0.1µF capacitor and at least a second  $V_{DD}$  input with a 1nF to 10nF capacitor (use a 0603 or smaller physical size ceramic capacitor).

\_\_\_\_Chip Information

PROCESS: BICMOS



### **Package Information**

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to <u>www.maxim-ic.com/packages</u>.)



**MAX4814E** 

M/IXI/M

## Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to **www.maxim-ic.com/packages**.)

				NFORM TO ANSI Y14.5-1982.
			DICATED AT I	MOLD PARTING LINE AND COINCIDENT WITH LEAD, WHERE LEAD EXITS
				DE MOLD PROTRUSION.
ALLO	WAB	LE MOLD PROT	RUSION IS 0.25	MM ON D1 AND E1 DIMENSIONS.
				AN THE BOTTOM OF PACKAGE BY 0.15 MILLIMETERS. AR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM
				N AT MAXIMUM MATERIAL CONDITION.
6. CONT	ROLI	ING DIMENSION	HILLIMETER.	
				JBLICATION 95 REGISTRATION MS-026, VARIATION ACD.
			NAR WITHIN .0	U4 INCH. R WITH BOTTOM OF PACKAGE WITHIN 2 MILS (.05 MM).
				) PAD (EP) VERSIONS ONLY, SEE INDIVIDUAL PRODUCT
DATA	SHE	ET TO DETERMI	NE IF A PRODU	JCT USES EXPOSED PAD PACKAGE.
/ <u>/11\</u> MARK	ING	SHOWN IS FOR	PACKAGE ORIE	INTATION REFERENCE ONLY.
l -				
	s		ARIATION	
	Ÿ M	ALL DIMENSIONS	IN MILLIMETERS	
	3	ACD	-HD	
	Ľ	MIN.	MAX.	
Γ	Α	<del>k</del> y	1.20	
	A1	0.05	0.15	
	Aa	0.95	1.05	
	D	11.80	12.20	
	D1	9.80	10.20	
	Е	11.80	12.20	
	E1	9.80	10.20	
	L	0.45	0.75	
	N	6	4	
	e	0.50	BSC.	
	ю	0.17	0.27	
	b1	0.17	0.23	
	с	0.09	0.20	
	c1	0.09	0.16	
	x	4.70	5.30	SEMICONDUCTOR
	Y	4.70	5.30	TITLE' PACKAGE OUTLINE,
-				64L TQFP, 10x10x1.0mm EP OPTION
	ΝΠΤ	TO SCALE-		APPRIVAL DOCUMENT CONTROL NO. REV. 2/2
		IL SCHLL		

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

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\_\_\_\_\_ 17